CY7C1059DV33

8-Mbit (1M x 8) Static RAM

Features

- High speed
  - t_{AA} = 10 ns
- Low active power
  - I_{CC} = 110 mA at 10 ns
- Low CMOS standby power
  - I_{SB2} = 20 mA
- 2.0V data retention
- Automatic power down when deselected
- TTL-compatible inputs and outputs
- Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features
- Available in Pb-free 44-pin TSOP II package

Functional Description

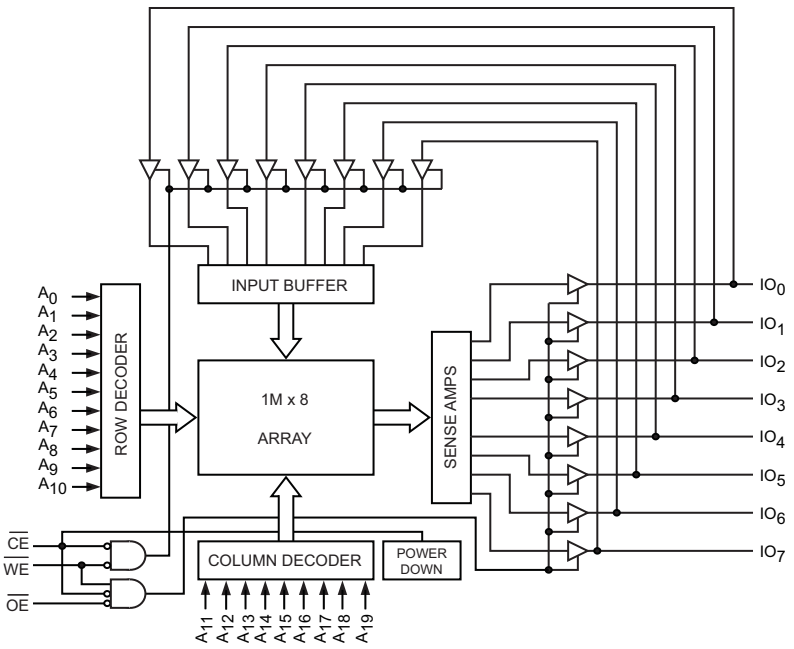
The CY7C1059DV33[1] is a high performance CMOS Static RAM organized as 1M words by 8 bits. Easy memory expansion is provided by an active LOW Chip Enable ($\overline{CE}$), an active LOW Output Enable ($\overline{OE}$), and tri-state drivers. To write to the device, take Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. Data on the eight IO pins (IO_0 through IO_7) is then written into the location specified on the address pins (A_0 through A_{19}).

To read from the device, take Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing Write Enable ($\overline{WE}$) HIGH. Under these conditions, the contents of the memory location specified by the address pins appear on the IO pins.

The eight input or output pins (IO_0 through IO_7) are placed in a high-impedance state when the device is deselected ($\overline{CE}$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), or a write operation is in progress ($\overline{CE}$ LOW, and $\overline{WE}$ LOW).

The CY7C1059DV33 is available in 36-ball FBGA and 44-pin TSOP II packages with center power and ground (revolutionary) pinout.

Logic Block Diagram

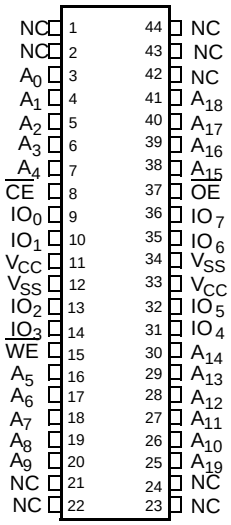


Note
1. For guidelines about SRAM system design, refer to the Cypress application note AN1064, SRAM System Guidelines available at www.cypress.com.

Pin Configuration

Figure 1. Pin Diagram - 44-Pin TSOP II

Top View



Selection Guide

	–10	–12	Unit
Maximum Access Time	10	12	ns
Maximum Operating Current	110	100	mA
Maximum CMOS Standby Current	20	20	mA

Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied ..... –55°C to +125°C

Supply Voltage on V_{CC} to Relative GND[2] .....–0.5V to +4.6V

DC Voltage Applied to Outputs in High-Z State[2] ..... –0.3V to V_{CC} + 0.3V

DC Input Voltage[2] ..... –0.3V to V_{CC} + 0.3V

Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage..... .....>2001V (MIL-STD-883, Method 3015)

Latch up Current..... >200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Industrial	–40°C to +85°C	3.3V ± 0.3V

Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions	–10		–12		Unit
			Min	Max	Min	Max	
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA	2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA		0.4		0.4	V
V_{IH}	Input HIGH Voltage		2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	V
V_{IL}	Input LOW Voltage[2]		–0.3	0.8	–0.3	0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}	–1	+1	–1	+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_{OUT} ≤ V_{CC}, Output Disabled	–1	+1	–1	+1	µA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., f = f_{MAX} = $1/t_{RC}$		110		100	mA
I_{SB1}	Automatic CE Power Down Current —TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH} V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}		40		35	mA
I_{SB2}	Automatic CE Power Down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f = 0		20		20	mA

Capacitance

Tested initially and after any design or process changes that may affect these parameters.]

Parameter	Description	Test Conditions	Max	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 3.3V	12	pF
C_{OUT}	IO Capacitance		12	pF

Thermal Resistance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	TSOP II	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	51.43	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		15.8	°C/W

Notes

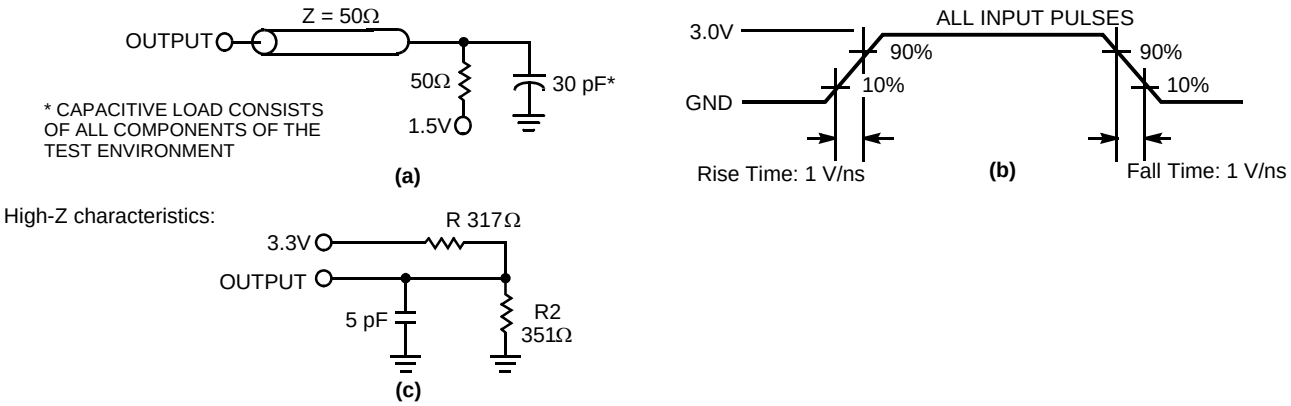
2. $V_{IL(min)}$ = –2.0V and $V_{IH(max)}$ = V_{CC} + 2V for pulse durations of less than 20 ns.
3. Tested initially and after any design or process changes that may affect these parameters.

[+] Feedback

AC Test Loads and Waveforms

AC characteristics (except High-Z) are tested using the load conditions shown in Figure 2 (a). High-Z characteristics are tested for all speeds using the test load shown in Figure 2 (c).

Figure 2. AC Test Loads and Waveforms

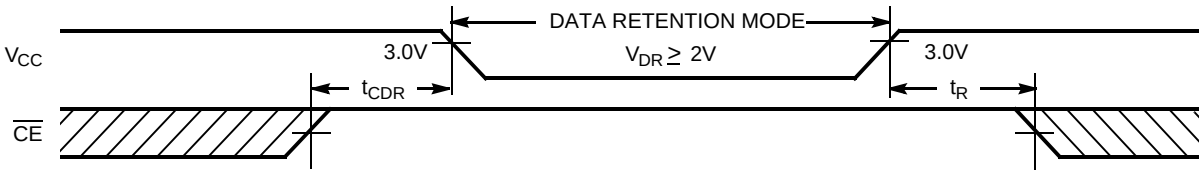


Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions[4]	Min	Max	Unit
V_{DR}	V_{CC} for Data Retention		2.0		V
I_{CCDR}	Data Retention Current	$V_{CC} = V_{DR} = 2.0V$, $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$		20	mA
t_{CDR}[3]	Chip Deselect to Data Retention Time		0		ns
t_R[5]	Operation Recovery Time		t_{RC}		ns

Data Retention Waveform



Notes

4. No inputs may exceed V_{CC} + 0.3V.
5. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)} \geq 50$ µs or stable at $V_{CC(min)} \geq 50$ µs.

[+] Feedback

AC Switching Characteristics

Over the Operating Range[6]

Parameter	Description	–10		–12		Unit
		Min	Max	Min	Max	
Read Cycle						
t_{power}[7]	V_{CC}(typical) to the First Access	100		100		µs
t_{RC}	Read Cycle Time	10		12		ns
t_{AA}	Address to Data Valid		10		12	ns
t_{OHA}	Data Hold from Address Change	2.5		2.5		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		10		12	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		5		6	ns
t_{LZOE}	$\overline{OE}$ LOW to Low-Z	0		0		ns
t_{HZOE}	$\overline{OE}$ HIGH to High-Z[8, 9]		5		6	ns
t_{LZCE}	$\overline{CE}$ LOW to Low-Z[9]	3		3		ns
t_{HZCE}	$\overline{CE}$ HIGH to High-Z[8, 9]		5		6	ns
t_{PU}	$\overline{CE}$ LOW to Power up	0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power down		10		12	ns
Write Cycle[10, 11]						
t_{WC}	Write Cycle Time	10		12		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	7		8		ns
t_{AW}	Address Setup to Write End	7		8		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Setup to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	7		8		ns
t_{SD}	Data Setup to Write End	5		6		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[9]	3		3		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[8, 9]		5		6	ns

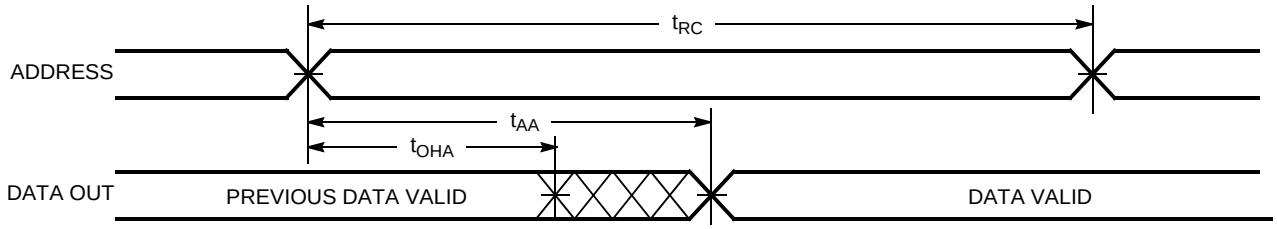
Notes

6. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V.
7. t_{POWER} is the minimum amount of time that the power supply must be at stable, typical V_{CC} values until the first memory access can be performed.
8. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (d) of "AC Test Loads and Waveforms" on page 4. Transition is measured when the outputs enter a high impedance state.
9. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
10. The internal write time of the memory is defined by the overlap of $\overline{CE}$ LOW, and $\overline{WE}$ LOW. $\overline{CE}$ and $\overline{WE}$ must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data setup and hold timing must refer to the leading edge of the signal that terminates the Write.
11. The minimum write cycle time for Write Cycle No. 3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.

Switching Waveforms

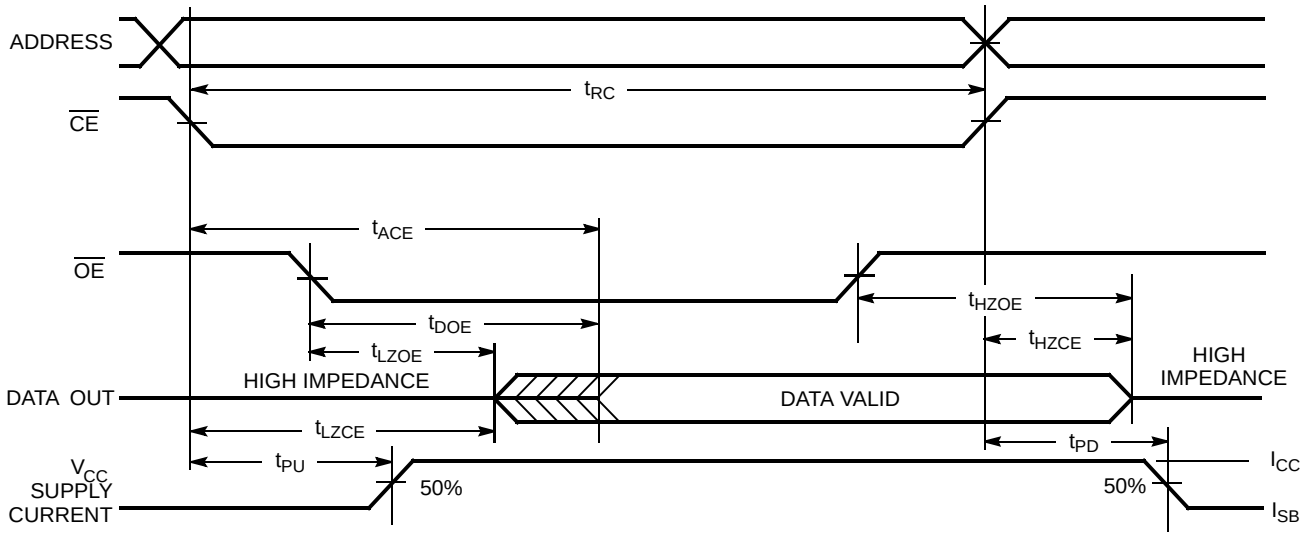
Read Cycle No. 1 (Address Transition Controlled)

Figure 3. Read Cycle No. 1[12, 13]



Read Cycle No. 2 ($\overline{OE}$ Controlled)

Figure 4. Read Cycle No. 2[13, 14]



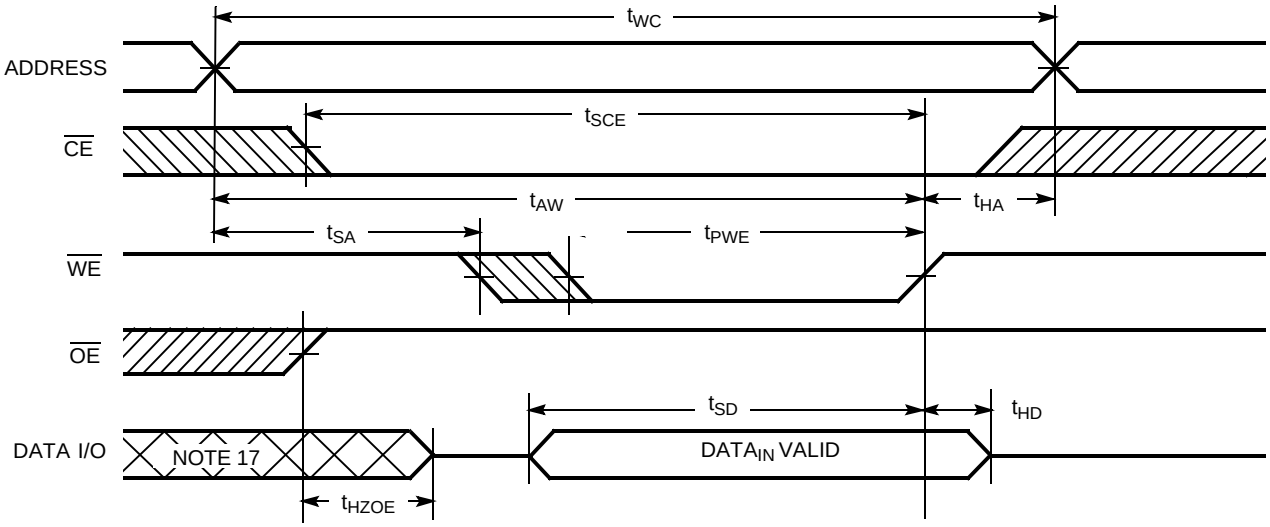
Notes
12. Device is continuously selected. $\overline{OE}$, $\overline{CE} = V_{IL}$.
13. $\overline{WE}$ is HIGH for Read cycle.
14. Address valid before or coincident with $\overline{CE}$ transition LOW.

[+] Feedback

Switching Waveforms(continued)

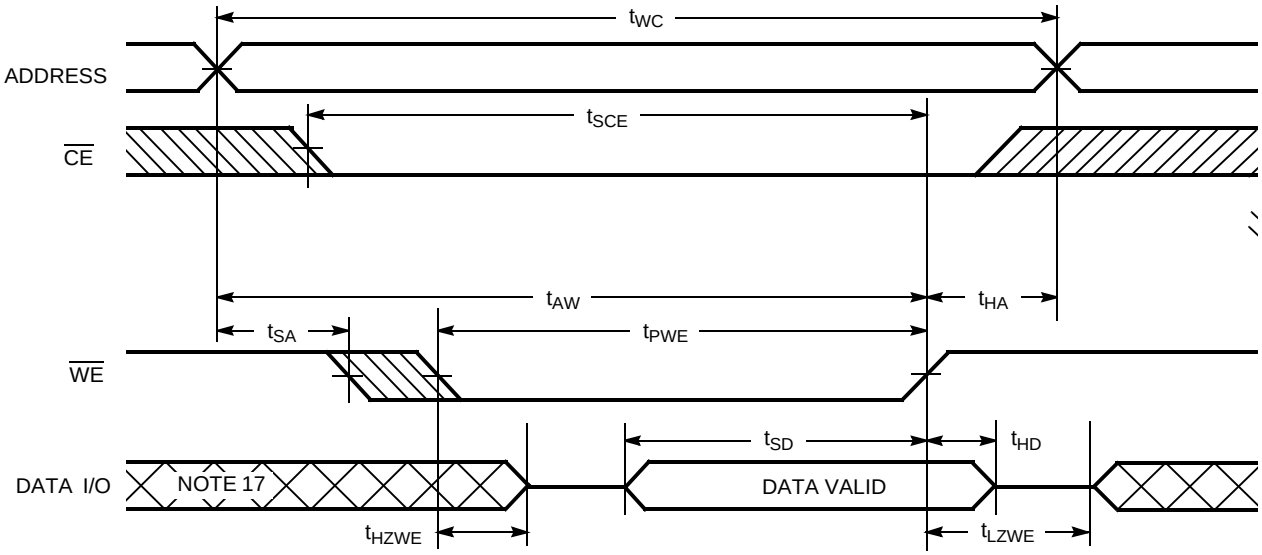
Write Cycle No. 1($\overline{WE}$ Controlled, $\overline{OE}$ HIGH During Write)

Figure 5. Write Cycle No. 1[15, 16]



Write Cycle No. 2 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)

Figure 6. Write Cycle No. 2[16]



Notes
15. Data IO is high-impedance if $\overline{OE}$ = V_{IH}.
16. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ going HIGH, the output remains in a high-impedance state.
17. During this period the IOs are in the output state and input signals must not be applied.

[+] Feedback

Truth Table

$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	IO_0–IO_7	Mode	Power
H	X	X	High-Z	Power Down	Standby (I_{SB})
L	L	H	Data Out	Read	Active (I_{CC})
L	X	L	Data In	Write	Active (I_{CC})
L	H	H	High-Z	Selected, Outputs Disabled	Active (I_{CC})

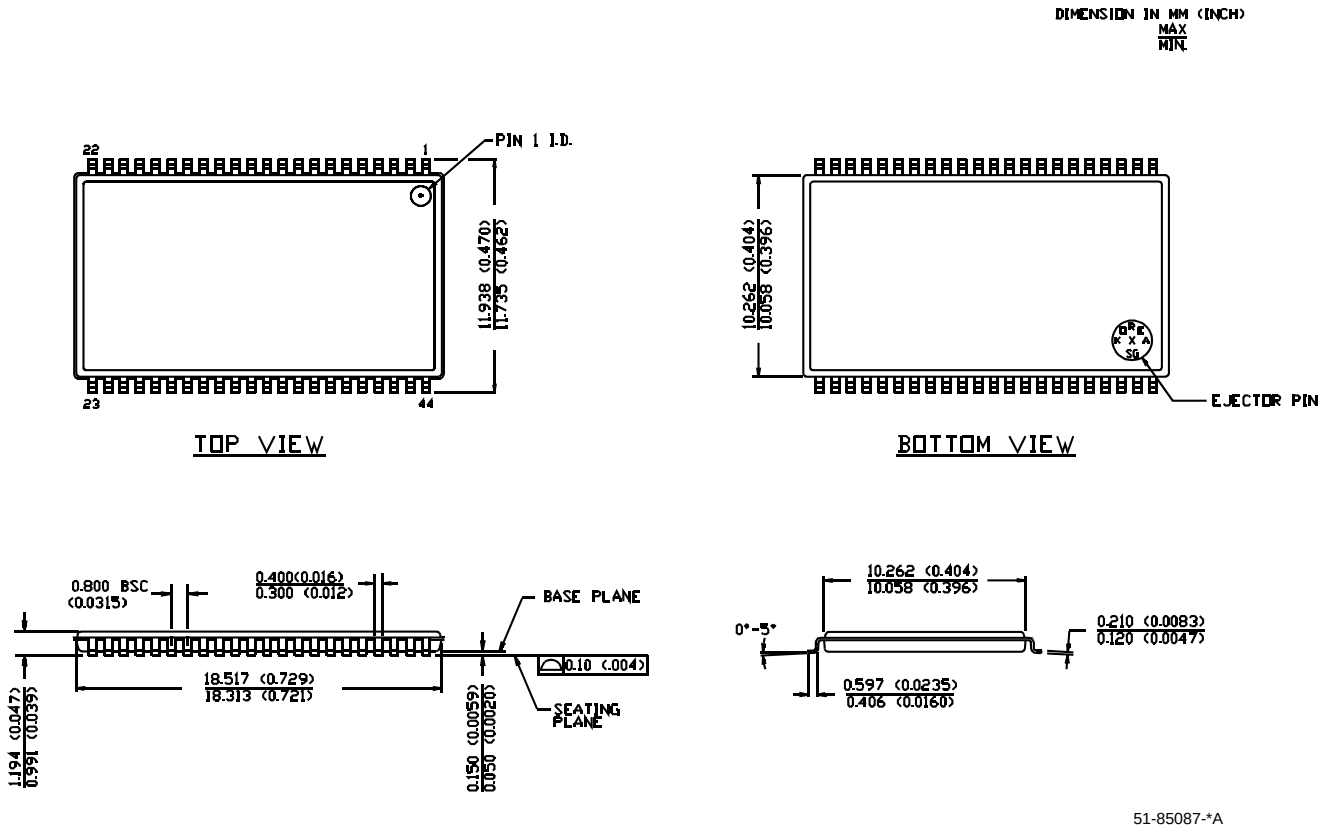
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C1059DV33-10ZSXI	51-85087	44-pin TSOP II (Pb-Free)	Industrial
12	CY7C1059DV33-12ZSXI	51-85087	44-pin TSOP II (Pb-Free)	

Contact your local Cypress sales representative for availability of these parts.

Package Diagrams

Figure 7. 44-Pin TSOP II (51-85087)



[+] Feedback

Document History Page

Document Title: CY7C1059DV33, 8-Mbit (1M x 8) Static RAM Document Number: 001-00061				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	342195	See ECN	PCI	New Data Sheet
*A	380574	See ECN	SYT	Redefined I_{CC} values for Com'l and Ind'l temperature ranges I_{CC} (Com'l): Changed from 110, 90 and 80 mA to 110, 100 and 95 mA for 8, 10 and 12 ns speed bins respectively I_{CC} (Ind'l): Changed from 110, 90 and 80 mA to 120, 110 and 105 mA for 8, 10 and 12 ns speed bins respectively Changed the Capacitance values from 8 pF to 10 pF on Page # 3
*B	485796	See ECN	NXR	Changed address of Cypress Semiconductor Corporation on Page# 1 from "3901 North First Street" to "198 Champion Court" Removed -8 and -12 Speed bins from product offering, Removed Commercial Operating Range option, Modified Maximum Ratings for DC input voltage from -0.5V to -0.3V and V_{CC} + 0.5V to V_{CC} + 0.3V Updated footnote #7 on High-Z parameter measurement Added footnote #11 Changed the Description of I_{IX} from Input Load Current to Input Leakage Current. Updated the Ordering Information table and Replaced Package Name column with Package Diagram.
*C	1513285	See ECN	VKN/AESA	Converted from preliminary to final Added 12 ns speed bin Changed C_{IN} and C_{OUT} specs from 16 pF to 12 pF Changed t_{OHA} spec from 3 ns to 2.5 ns Updated Ordering information table

© Cypress Semiconductor Corporation, 2005-2007. The information contained herein is subject to change without notice. Cypress Semiconductor Corporation assumes no responsibility for the use of any circuitry other than circuitry embodied in a Cypress product. Nor does it convey or imply any license under patent or other rights. Cypress products are not warranted nor intended to be used for medical, life support, life saving, critical control or safety applications, unless pursuant to an express written agreement with Cypress. Furthermore, Cypress does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress products in life-support systems application implies that the manufacturer assumes all risk of such use and in doing so indemnifies Cypress against all charges.

Any Source Code (software and/or firmware) is owned by Cypress Semiconductor Corporation (Cypress) and is protected by and subject to worldwide patent protection (United States and foreign), United States copyright laws and international treaty provisions. Cypress hereby grants to licensee a personal, non-exclusive, non-transferable license to copy, use, modify, create derivative works of, and compile the Cypress Source Code and derivative works for the sole purpose of creating custom software and or firmware in support of licensee product to be used only in conjunction with a Cypress integrated circuit as specified in the applicable agreement. Any reproduction, modification, translation, compilation, or representation of this Source Code except as specified above is prohibited without the express written permission of Cypress.

Disclaimer: CYPRESS MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARD TO THIS MATERIAL, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE. Cypress reserves the right to make changes without further notice to the materials described herein. Cypress does not assume any liability arising out of the application or use of any product or circuit described herein. Cypress does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress' product in a life-support systems application implies that the manufacturer assumes all risk of such use and in doing so indemnifies Cypress against all charges.

Use may be limited by and subject to the applicable Cypress software license agreement.

All products and company names mentioned in this document may be the trademarks of their respective holders.

[+] Feedback